EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	6397	electron beam evaporation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 13:45
S2	229	S1 with glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 17:37
S3	7612	electron beam evaporation or e beam evaporation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:41
S4	225	S3 and hermetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:31
S5	10	S3 same hermetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:31
S6	3	"4104418".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:35
S7	3	("4104418").URPN.	USPAT	ADJ	ON	2005/10/12 18:36
S8	16	("3276902" | "3801356" | "3836393" | "4104418" | "4374391" | "4407061").PN. OR ("4731293"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/12 18:52
S9	20	("2084747" | "3432417" | "3837866" | "3885975" | "3888685" | "4091171").PN. OR ("4407061"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/13 11:30
S10	1866	electron beam (evaporation deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:42

EAST Search History

S11	10682	electron beam (evaporation or deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:11
S12	1	S11 same negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S13	113	S11 and negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S14	1383	S11 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S15	6	S14 and negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35
S16	80	427/473.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:54
S17	248	427/504.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:34
S18	1189	427/585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:34
S19	438	S14 and $5resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35
S20	152	S14 same $5resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35

EAST Search History

S21	10682	electron beam (evaporation or deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:12
S22	1084	S21 same (metal$3 near5 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:14
S23	230	S22 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:05
S24	149	S21 same (metal$3 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S25	7	S24 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:14
S26	1018	S21 with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S27	24	S26 same (metal$3 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S28	20	("4617192" | "4749255").PN. OR ("5451548").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/14 11:06
S31	107	plasma ion assisted deposition or PIAD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:30
S33	7	S31 same (glass or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 11:12

EAST Search History

S34	107	plasma ion assisted deposition or PIAD or plasma ion-assisted deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:31
S35	7	S34 same (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:36
S36	20999	evaporation with (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:43
S37	49	S36 with metal$3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:43
S38	3	S37 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:37
S39	19	S37 and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44
S40	3	S39 and (chemical mechanical polishing or cmp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:38
S41	40042	evaporat$3 with (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:30
S42	98	S41 with metal$3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:31
S43	42	S42 and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44

S44	23	S43 not S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44
S45	40908	evaporat$3 with (oxide or glass or dielectric or silicate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:30
S46	4925	S45 with (copper or aluminum or tungsten or metal$3 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:32
S47	130	S45 with ((copper or aluminum or tungsten or metal$3) substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:33
S48	16	S47 and planar$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:37
S49	2	"4827870".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:38
S50	2	"4793980".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:59
S51	16	dielectric over metal and cmp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:12
S52	46	resistor same platinum same passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:14
S53	1	S52 and cmp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:13

S54	1252	resistor same platinum same (passivat$3 or barrier or dielectric or oxide or glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:15
S56	0	S54 same (cmp or chemical mechanical polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S57	28	S54 and (cmp or chemical mechanical polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:15
S58	149	S54 same etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S59	16	S58 same evaporat$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S60	5	("5543775").URPN.	USPAT	ADJ	ON	2005/10/14 18:08
S61	113	electron beam evaporation and moving substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:25
S62	11	electron beam evaporation same moving substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:38
S63	3	cmp passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:39
S64	692	cmp same passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:40

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S65	372	cmp with passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:40
S66	8348	(electron beam or ebeam or e beam) (evaporation or vaporization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 13:46
S67	8348	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 13:47
S68	11577	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:03
S69	0	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same binary glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:48
S70	3	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) and binary glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:16
S71	12	("4407061").URPN.	USPAT	ADJ	ON	2006/03/23 14:06
S72	6	(electron beam or ebeam or e beam or e-beam) and binary glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:23
S73	3	S72 not S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:21
S74	55059	(electron beam or ebeam or e beam or e-beam) and glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:11

EAST Search History

S75	42779	(electron beam or ebeam or e beam or e-beam) and glass and (metal or copper or cu or titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:24
S76	9095	(electron beam or ebeam or e beam or e-beam) same glass and (metal or copper or cu or titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:34
S77	3855	(electron beam or ebeam or e beam or e-beam) same glass same (metal or copper or cu or titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:25
S78	804	(electron beam or ebeam or e beam or e-beam) with glass with (metal or copper or cu or titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:25
S79	24	S78 and hermetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:26
S80	38	(electron beam or ebeam or e beam or e-beam) same phosphosilicate glass and (metal or copper or cu or titanium or ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:34
S81	105	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:48
S82	0	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same passivation layer same (phosphosilicate glass or psg)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:50
S83	10	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same passivation layer same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:52
S84	482	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) with glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 15:49

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S85	879623	packag$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 15:48
S86	35352	S85 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 15:49
S87	296	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) and S86	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 15:49
S88	1	("5379186").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 15:54
S89	6	("6194789").URPN.	USPAT	ADJ	ON	2006/03/23 15:56
S90	1	"5262364".pn.	USPAT	ADJ	ON	2006/03/23 15:56
S91	10	("5262364").URPN.	USPAT	ADJ	ON	2006/03/23 16:03
S92	12	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same hermetic seal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:07
S93	7	("2922076" | "3512041" | "4266223" | "5239227" | "5525867").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 16:05
S94	7	("2922076" | "3512041" | "4266223" | "5239227" | "5525867").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 16:06
S95	12	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same hermetic seal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 17:39
S96	30	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same glass and hermetic seal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:11

EAST Search History

S97	18	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same hermetic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:33
S98	6	S97 not S95	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:12
S99	52	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) with passivation layer .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:45
S10 0	488	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) with glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:46
S10 1	4	S100 same passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:47
S10 2	2	"4819039".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 16:47
S10 3	20	("2106744" | "2221709" | "3054221" | "4228446" | "4374391" | "4492717").PN. OR ("4819039"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 16:48
S10 4	28	("3804738" | "3825442" | "3887733" | "3899372" | "3925572" | "3983022" | "4045594" | "4183135" | "4204894" | "4224089" | "4251571" | "4271582" | "4305974").PN. OR ("4492717"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 16:56
S10 5	7	("3475210" | "4045594" | "4417914" | "4468437" | "4492717" | "4508757").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/23 17:17

EAST Search History

S10 6	29	("4045594").URPN.	USPAT	ADJ	ON	2006/03/23 17:25
S10 7	2005	metal line with (dielectric or glass)	USPAT	ADJ	ON	2006/03/23 17:25
S10 8	30	metal line with (dielectric or glass) near2 coat$3	USPAT	ADJ	ON	2006/03/23 17:39
S10 9	0	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) same metal line with (dielectric or glass)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:23
S11 0	67	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) and metal line with (dielectric or glass)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 18:11
S11 1	110	metal line with (dielectric or glass) and oxide near3 fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:54
S11 2	86	silicon oxynitride with graded	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:56
S11 3	32	S112 and $5resist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:10
S11 4	39002	(circuit board or pcb) with (metal or aluminum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:11
S11 5	23	S114 and (electron beam or ebeam or e beam or e-beam) with glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:30

EAST Search History

S11 6	1293	(vaporization or evaporation) with glass and (aluminum or metal) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:32
S11 7	323	(vaporization or evaporation) with glass and (aluminum or metal) substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:05
S11 8	6015	glass near2 coat$3 near2 (metal or aluminum or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:06
S11 9	234	glass near2 coat$3 near2 (metal or aluminum or copper) same (vaporiz$6 or evaporat$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:13
S12 0	327	(glass or oxide) near2 (vaporiz$6 or evaporat$5 or deposit$4) with (metal or aluminum or copper or tungsten or titanium) (substrate or workpiece)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:15
S12 1	15	("1845231" | "3075902" | "3312893" | "3378676" | "3669868" | "3692987" | "3975681" | "4038532" | "4047029" | "4196475" | "4310389").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/24 11:16
S12 2	10	("3493404" | "3964918" | "4256796" | "4343908" | "4385127" | "4557862" | "4742028").PN. OR ("4965229").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/24 11:20
S12 3	68	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) with (dielectric or glass or oxide) and (circuit board or pcb)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 12:12
S12 4	11442	hermetic seal	USPAT	ADJ	ON	2006/03/24 11:24
S12 5	9641	pattern$3 near2 (glass or dielectric or oxide) same $5resist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:39

S12 6	12	S125 same (metal or aluminum or steel) substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:38
S12 7	13	S125 same (metal or aluminum or steel or copper) substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:38
S12 8	1	S127 not S126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:38
S12 9	124	pattern$3 near2 (glass or dielectric or oxide) same (metal or aluminum or steel or copper) substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 11:39
S13 0	42	(electron beam or ebeam or e beam or e-beam) (evaporation or vaporization or deposition) with (dielectric or glass or oxide) same capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 12:38
S13 1	13	negative relief mask or reverse photolithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 13:14
S13 2	0	2002/0084885	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 13:14
S13 3	2	"20020084885"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 13:14